IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Kie Y. Ahn et al.

Title: METHODS FOR MAKING INTEGRATED-CIRCUIT WIRING FROM COPPER, SILVER,

GOLD, AND OTHER METALS

Docket No.:

303.648US1

Filed:

January 18, 2000

Examiner:

Neal Berezny

Commissioner for Patents

P.O.Box 1450

Alexandria, VA 22313-1450

Serial No.: 09/484303 Due Date: June 30, 2003 Group Art Unit: 2823

JUL -8 2003

We are transmitting herewith the following attached items (as indicated with an "X"):

 \underline{X} A return postcard.

X A Response under 37 CFR 1.111 (2 Pages).

X A Supplemental Information Disclosure Statement (1 pg.), Form 1449 (3 pgs.), and copies of 68 cited documents.

X A check in the amount of \$180.00 to cover the fee for consideration of Supplemental Information Disclosure Statement under 97(c).

If not provided for in a separate paper filed herewith, Please consider this a PETITION FOR EXTENSION OF TIME for sufficient number of months to enter these papers and please charge any additional fees or credit overpayment to Deposit Acc unt No. 19-0743.

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.

P.O. Box 2938, Minneapolis, MN 55402 (612-373-6900)

Atty. Eduardo E. Drake Reg. No. 40,594

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Commissioner for Patents, P.O.Box 1450, Alexandria, VA 22313-1450, on this day of June, 2003.

Name

Gina M. Uphus

Signatur

Customer Number 21186

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.

P.O. Box 2938, Minneapolis, MN 55402 (612-373-6900)

(GENERAL)

S/N 09/484303

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Examiner: Neal Berezny

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January 18, 2000

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Title:

METHODS FOR MAKING INTEGRATED-CIRCUIT WIRING FROM

COPPER, SILVER, GOLD, AND OTHER METALS

RESPONSE UNDER 37 CFR § 1.111

Commissioner for Patents P.O.Box 1450 Alexandria, VA 22313-1450

Interview Summary

In response to the Office Action mailed on March 31, 2003, applicant's patent counsel Eduardo Drake interviewed Ex. Berezney on June 27, 2003. The focus of the interview was the fact that the Office Action did not reflect applicant's earlier facsimile filing of a Preliminary Amendment on March 12, 2003. Agreement was reached that a new, superceding non-final Office Action reflecting the Preliminary Amendment would be prepared and mailed in due course.

Applicant further notes that a Supplemental Information Disclosure Statement accompanies this paper, and requests respectfully that the Examiner consider the associated references in preparation of the new, non-final Office Action.

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JUL -8 2003
TECHNOLOGY CENTER 2800

Serial Number: 09/484303

Filing Date: January 18, 2000

Title: METHODS FOR MAKING INTEGRATED-CIRCUIT WIRING FROM COPPER, SILVER, GOLD, AND OTHER METALS

CONCLUSION

The Examiner is invited to telephone Applicant's attorney at (612) 349-9593 to facilitate prosecution of this application.

If necessary, please charge any additional fees or credit overpayment to Deposit Account No. 19-0743

Respectfully submitted,

KIE Y. AHN ET AL.

By their Representatives,

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.

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612-349-9592

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Gina M. Uphus

Name

Signature

PATENT

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:

Kie Y. Ahn et al.

Examiner:

Neal Berezny

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2823

Fi**le**d:

January 18, 2000

Docket:

303.648USE

METHODS FOR MAKING INTEGRATED-CIRCUIT WIRING FROM COPESILVER, GOLD, AND OTHER METALS

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Assistant Commissioner for Patents P.O.Box 1450 Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 et. seq., the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Supplemental Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. §1.97(c)(2), Applicants have included the fee of \$180.00 as set forth in 37 C.F.R. §1.17(p). Please charge any additional fees or credit any overpayment to Deposit Account No. 19-0743.

The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

Respectfully submitted,

07/07/2003 GWORDOF1 00000078 09484303

01 FC:1806

180.00 OP

KIE Y. AHN ET AL.

By their Representatives,

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.

P.O. Box 2938

Minneapolis, MN 55402

612-349-9593

Date 30 Jun 2003

Eduardo E. Drake Reg. No. 40,594

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Gina M. Uphus

Signature

Name

Substitute for form 1449A/PTO Complete if Known INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as declessary) **Application Number** 09/484303 January 18, 2000 **Filing Date** Ahn, Kie **First Named Inventor** JUL O 3 2003 **Group Art Unit** 2823 **Examiner Name** Berezny, Neal Sheet 1 of 3 Attorney Docket No: 303.648US1

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EXAMINER

DATE CONSIDERED

Substitute for form 1449A/PTO Complete if Known INFORMATION DISCLOSURE **Application Number** 09/484303 STATEMENT BY APPLICANT (Use as many sheets as necessary) **Filing Date** January 18, 2000 'Ahn, Kie THE B 3 SOLD First Named Inventor **Group Art Unit** 2823 **Examiner Name** Berezny, Neal Attorney Docket No: 303.648US1 Sheet 2 of 3

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Substitute for form 1449A/PTO Complete if Known INFORMATION DISCLOSURE STATEMENT BY APPLICANT
Use as many sheets as necessary **Application Number** 09/484303 January 18, 2000 Filing Date Ahn, Kie **First Named Inventor Group Art Unit** 2823 **Examiner Name** Berezny, Neal Attorney Docket No: 303.648US1 Sheet 3 of 3

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